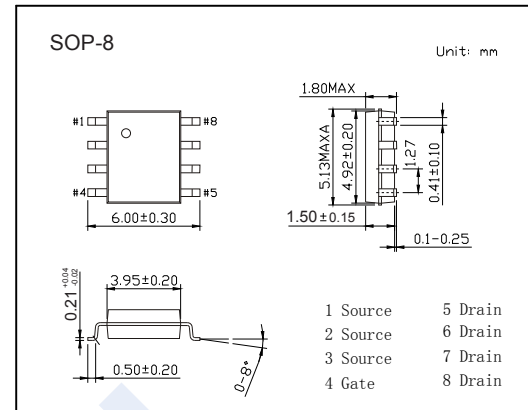
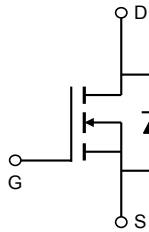


N-Channel MOSFET

AO4402 (KO4402)

■ Features

- $V_{DS} (V) = 20V$
- $I_D = 20 A (V_{GS} = 4.5V)$
- $R_{DS(ON)} < 5.5m\Omega (V_{GS} = 4.5V)$
- $R_{DS(ON)} < 7m\Omega (V_{GS} = 2.5V)$



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit	
Drain-Source Voltage	V_{DS}	20	V	
Gate-Source Voltage	V_{GS}	± 12		
Continuous Drain Current	I_D	$T_A=25^\circ C$	20	
		$T_A=70^\circ C$		16
Pulsed Drain Current	I_{DM}	140	A	
Avalanche Current	I_{AS}, I_{AR}	57		
Avalanche energy	$L=0.1mH$	E_{AS}, E_{AR}	162	mJ
Power Dissipation	P_D	$T_A=25^\circ C$	3.1	W
		$T_A=70^\circ C$	2	
Thermal Resistance.Junction- to-Ambient	R_{thJA}	$t \leq 10s$	40	$^\circ C/W$
		Steady-State	75	
Thermal Resistance.Junction- to-Lead	R_{thJL}	24		
Junction Temperature	T_J	150	$^\circ C$	
Storage Temperature Range	T_{stg}	-55 to 150		

N-Channel MOSFET

AO4402 (KO4402)

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V _{DSS}	I _D =250 uA, V _{GS} =0V	20			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =20V, V _{GS} =0V			1	uA
		V _{DS} =20V, V _{GS} =0V, T _J =55°C			5	
Gate-Body Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±12V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	0.5		1.6	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =4.5V, I _D =20A			5.5	mΩ
		V _{GS} =4.5V, I _D =20A, T _J =125°C			7	
		V _{GS} =2.5V, I _D =18A			7	
On State Drain Current	I _{D(ON)}	V _{GS} =10V, V _{DS} =5V	140			A
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =20A		105		S
Input Capacitance	C _{iss}	V _{GS} =0V, V _{DS} =10V, f=1MHz	3080		4630	pF
Output Capacitance	C _{oss}		520		960	
Reverse Transfer Capacitance	C _{rss}		350		810	
Gate Resistance	R _g	V _{GS} =0V, V _{DS} =0V, f=1MHz	0.6		2.1	Ω
Total Gate Charge	Q _g	V _{GS} =10V, V _{DS} =10V, I _D =20A	28		43	nC
Gate Source Charge	Q _{gs}		7		11	
Gate Drain Charge	Q _{gd}		7		17	
Turn-On DelayTime	t _{d(on)}	V _{GS} =10V, V _{DS} =10V, R _L =0.5Ω, R _{GEN} =3Ω		7		ns
Turn-On Rise Time	t _r			8		
Turn-Off DelayTime	t _{d(off)}			70		
Turn-Off Fall Time	t _f			18		
Body Diode Reverse Recovery Time	t _{rr}	I _F = 20A, di/dt= 500A/us	13		20	nC
Body Diode Reverse Recovery Charge	Q _{rr}		29		43	
Maximum Body-Diode Continuous Current	I _S				4	A
Diode Forward Voltage	V _{SD}	I _S =1A, V _{GS} =0V			1	V

Note : The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.

■ Marking

Marking	4402
	KC****

N-Channel MOSFET AO4402 (KO4402)

■ Typical Characteristics

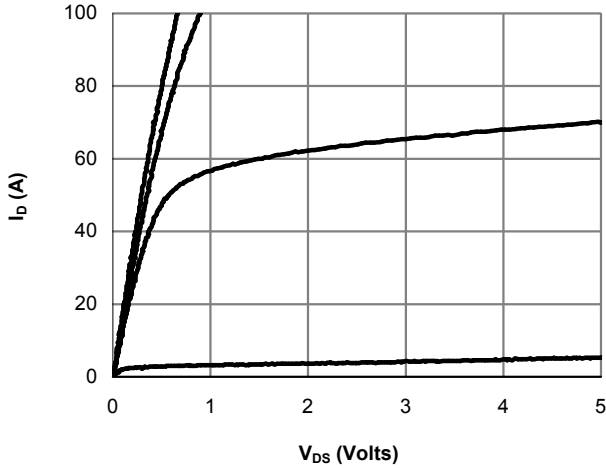


Fig 1: On-Region Characteristics (Note E)

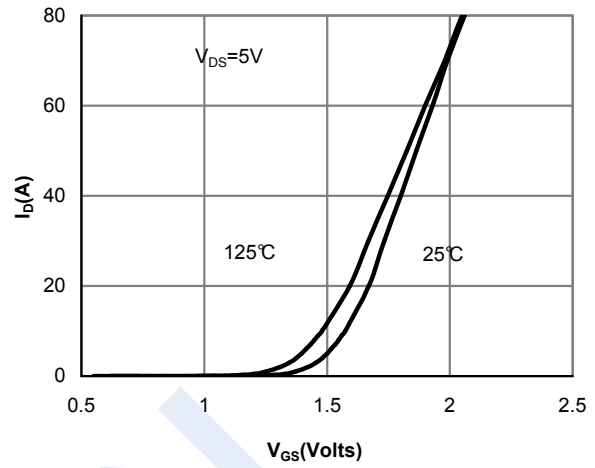


Figure 2: Transfer Characteristics (Note E)

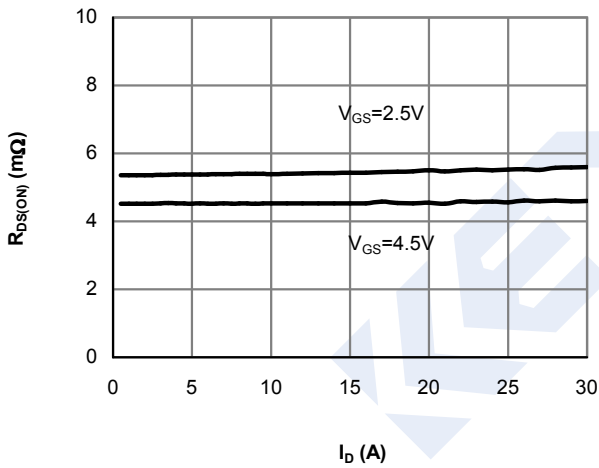


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

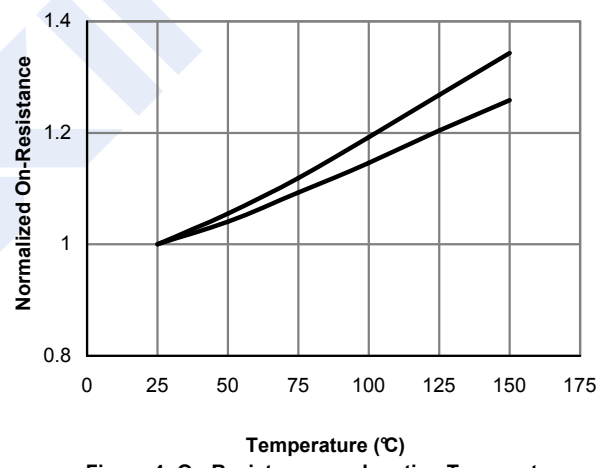


Figure 4: On-Resistance vs. Junction Temperature (Note E)

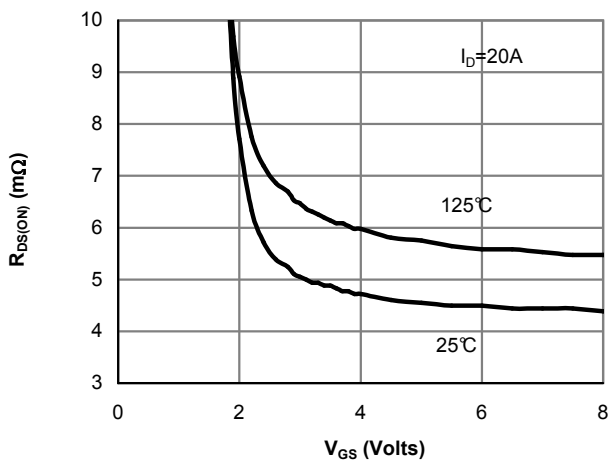


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

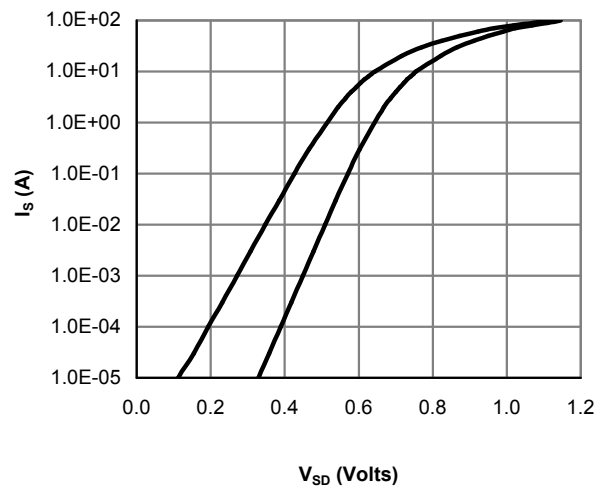


Figure 6: Body-Diode Characteristics (Note E)

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■ Typical Characteristics

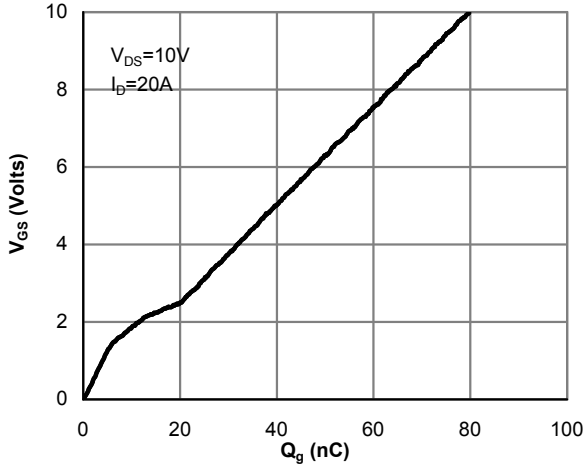


Figure 7: Gate-Charge Characteristics

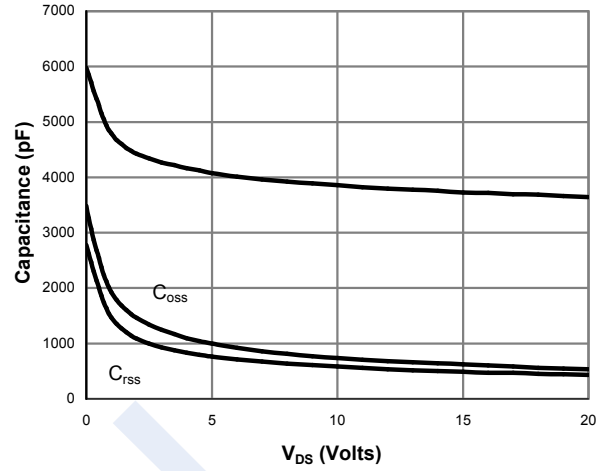


Figure 8: Capacitance Characteristics

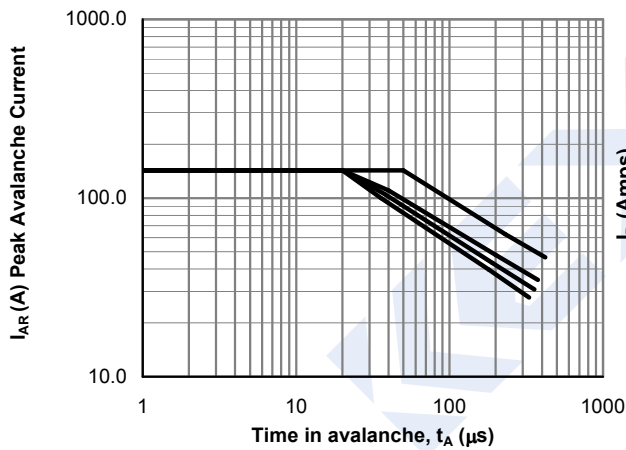
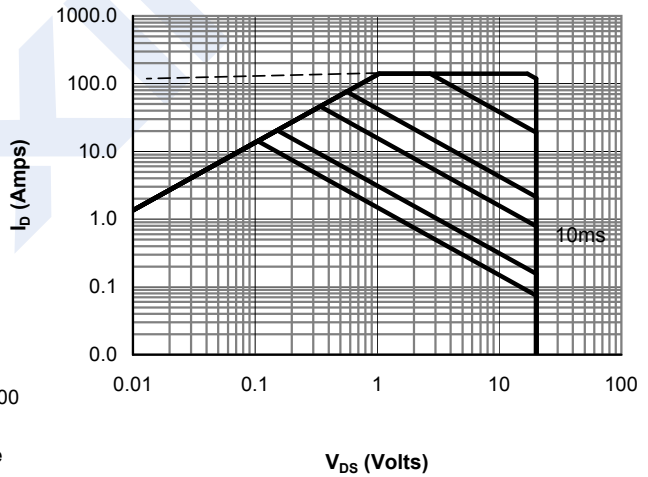


Figure 9: Single Pulse Avalanche capability (Note C)



V_{DS} (Volts)

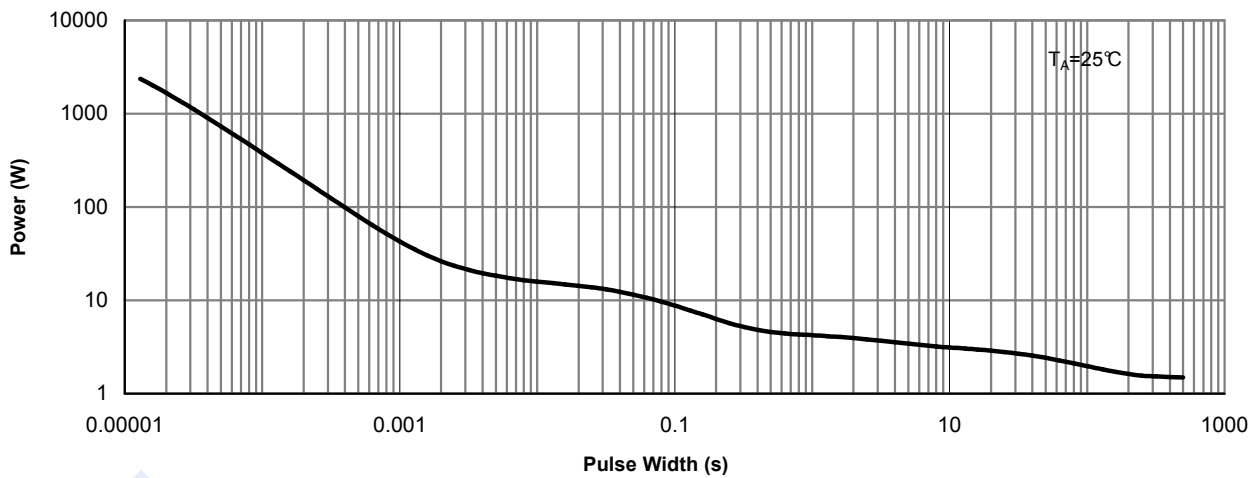


Figure 11: Single Pulse Power Rating Junction-to-Ambient (Note F)

N-Channel MOSFET AO4402 (KO4402)

■ Typical Characteristics

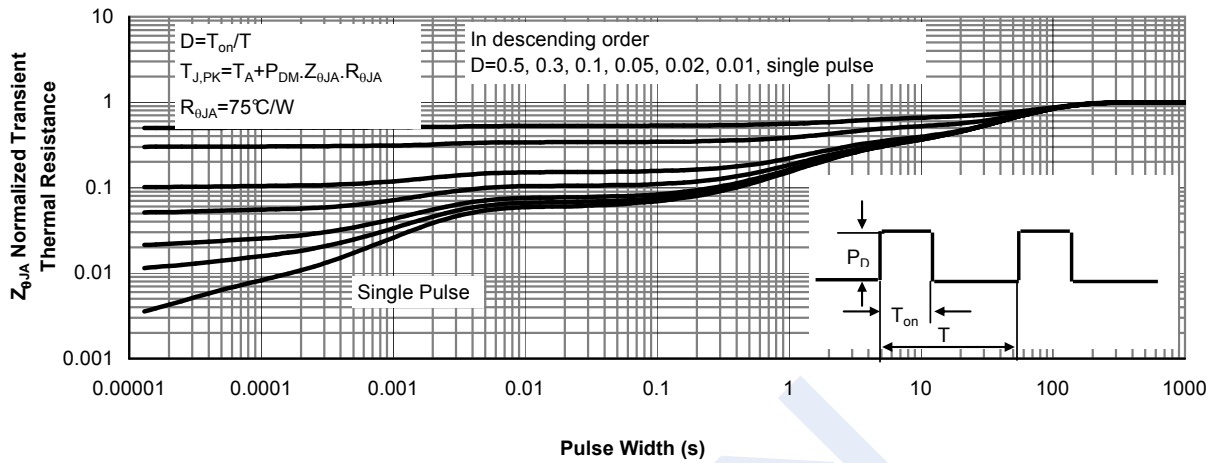


Figure 12: Normalized Maximum Transient Thermal Impedance (Note F)